

# **Efect of ZnO doping co‑carried out by Co–Cu on nonlinear optical properties prepared by the spin coating method**

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# **Abstract**

In the present work, thin flms of ZnO co-doped with Co and Cu cations were obtained on glass substrate, combining the sol gel process and spin-coating technique. For the compound, the general chemical formula used was:  $Zn_{1-x-z}Co_xCu_zO$ ,  $[(x; z)=(0.00; 0.00),$ (0.02; 0.02), (0.04; 0.04) and (0.06; 0.06)]. For pure ZnO flm, the surface morphology is composed by small spherical grains that present interstitial spaces, while the flms obtained from the simultaneous Co and Cu insertion in the ZnO structure are more dense and interstitial spaces disappear. For all flms, the X-ray difraction patterns testify the monophasic phase formation, typical of the hexagonal structure of ZnO. In addition, the flms presented preferential orientation in the (002) direction. It was demonstrated that the  $\text{Zn}^{2+}$  cations by  $Co<sup>2+</sup>$  and  $Cu<sup>2+</sup>$  cations replacement, causes relevant modifications in the lattice parameter (c), crystallite size (D), dislocation density (δ), strain ( $\varepsilon_c$ ) and stress ( $\sigma_c$ ) of the hexagonal structure wurtzite from ZnO. The Co and Cu cations inclusion in the ZnO host lattice, alto caused a decrease in the optical band gap energy (3.37 for 3.16 eV), which is related to the charge transfer between the 4f level electrons and the conduction band or valence band of ZnO. Finally, for all flms thin the linear and non-linear optical constants were computed and analyzed, showing variations that depend on the concentration of the dopant cations.

**Keywords** (Co–Cu) co-doped ZnO · Thin flms · Sol–gel process · Spin coating · XRD patterns

# **1 Introduction**

The importance of linear and non-linear optical semiconductors (NLOs) lies in the optical properties within which light is propagated. Therefore, they are used in various applications such as: optical waveguides, optoelectronic apparatuses, optical switching, image treatment, optical signal processing, optical enquiry stocking, optical locating, high-speed optical connections, and after time appliances in biological and medical sciences (Nagaraja et al. [2013\)](#page-13-0).

Zinc oxide (ZnO) thin flms are extensively studied because they have high photoelectric possessions, high electrochemical stability andenergy gap  $(E_{g}=3.37eV)$  at

Extended author information available on the last page of the article

room temperature (Yan et al. [2020](#page-14-0)). The ZnO doped and codoped with diferent cations is inspected as an excellent strategy for changes and improves various physical properties such as, crystalline quality, reducing crystal defects and modulating the energy gap (Kompa et al. [2023](#page-13-1); Andriotis and Menon [2015](#page-11-0); Chaitra et al. [2017;](#page-12-0) Mohammedi et al. [2022\)](#page-13-2). The ZnO properties have been studied from the insertion of a simple cations: Fe(Hadimani et al. [2018\)](#page-12-1), Mg(Mahroug et al. [2019\)](#page-13-3), Ni (Oudjertli et al. [2022](#page-13-4)), Al (Islam et al. [2019\)](#page-13-5), Cu (Mohammedi et al. [2021\)](#page-13-6), Al, Cu, Co and In (Kim et al. [2015\)](#page-13-7), and with two simultaneous cations such as: (Co–Al) and (Ni–Cu) (Swapna and Reddy [2018](#page-14-1); Ali et al. [2018\)](#page-11-1), (Y–Fe) (Peña-Garcia et al. [2020\)](#page-13-8), (Ni–Sr) (Peña-Garcia et al. [2019](#page-14-2)), (Fe–Pr) (Rocha et al. [2023\)](#page-14-3), (Ni–Ce) (Costa-Silva et al. [2022\)](#page-12-2) and (Er–Cr) (França et al. [2023](#page-12-3)) Also, Goktas et al. [\(2018](#page-12-4)) reported the structural, optical and magnetic properties Co–Cu doped ZnO thin flms that was annealed in air and argon atmosphere. The NLOand ZnO thin flms doped with Na (Deekshitha et al. [2019](#page-12-5)), Zr (Bahedi et al. [2009a\)](#page-12-6), and Ce (Chen et al. [2020\)](#page-12-7) have demonstrated optical improved properties (Peng et al. [2018\)](#page-13-9).

Other simple oxides, such as CoO, have been studied by Z-Scan by various researchers (Chouhan et al. [2017\)](#page-12-8). Also, the study of NLO properties of ZnO structures by Z-Scan has been madeby diferent authors (Mostafa et al. [2021](#page-13-10)). For example, Mustafa et al. examined the NLO properties of ZnO samples doped and co-doped with Zn and Ag prepared with PLD technique. They reported an enhancement in the NLO properties for the Ag/Zn/ZnO co-doped sample, which may be suitable for optical applications (Ali et al. [2018](#page-11-1)). Furthermore, non-linear optical response  $\chi^{(3)} = 20.12 \times 10^{-12}$  on Zr- doped ZnO films utilizing the spray pyrolysis technique was reported (Bahedi et al. [2009b](#page-12-9)**).**

Based on this argument, in this work, Co-Cuco-doped ZnO thin flms have been obtained on glass substrate, combining the sol–gel method and spin-coating technique. Specifcally, films were obtained from the compound with general chemical formula:  $Zn_{1-x}C_0$ ,  $Cu$ ,  $O$ ,  $[(x; z) = (0.00; 0.00), (0.02; 0.02), (0.04; 0.04)$  and  $(0.06; 0.06)$ ]. We focused on the study of the simultaneous addition of Co and Cu cations on the morphological, structural, and optical linear and non-linear properties (second-degree refractive index and third-degree electrical susceptibility). Our study aims to amplify the optical applications of these flms, specifcally, in the transparent conductor screen.

# **2 Experimental method**

#### **2.1 Method of preparation**

For synthesis, we used the general chemical formula:  $Zn_{1-x}zC_0xCu_2O$ ,  $[(x; z)=(0.00;$ 0.00), (0.02; 0.02), (0.04; 0.04) and (0.06; 0.06)].We prepared a solution of initial concentration ( $C_T$ =0.5 M) and initial volume ( $V_T$ =10ml). The raw materials, Zinc acetate dehydrates [Zn  $(CH_3COO_22H_2O]$ , Cobalt (II) chloride dihydrate (CoCl<sub>2</sub>.H<sub>2</sub>O), and Copper (II) chloride dihydrate (CuCl<sub>2</sub>.H<sub>2</sub>O) were dissolved in 2-propanol by constant agitation. The Monoethanolamine (MEA) was used as a stabilizer in the solution. The solution was mixer at 65°C for 2 h and then left for 24 h at room temperature. The glass substrates were cleaned with ethanol and acetone for 10 min and dried. The sol was transformed in crystalline films using the spin coating technique (3000 rpm), with a heat treatment at 250 °C for 4 min to steam the solvents and organic residuum and then, at 500 °C. All samples were prepared under the same conditions, respecting the mixing at the atomic level.

# **2.2 Characterization method**

The morphologies of the flms were studied from images obtained in a FEI quanta FEG 200 (FESEM) feld-emitting scanning electron microscope (30 kV) and equipped with an energy-dispersion X-ray (EDAX). The XRD patterns were measurement using a Rigaku Ultima IV diffractometer in the Bragg–Brentano configuration utilizing  $CuK\alpha$  radiation ( $\lambda$ =1.54060 Å). The optical properties were analyzed by measurement obtained in a UV–visible spectrophotometer, Lambda 35 model (range of 300–800 nm). The transmission (T) and absorption (A) ranges are steeped, while the refectance (R) is calculated using the formula:  $R=1-(T+A)$ . Finally, the film thickness is measured by using the Claw-Tencor Alpha-Step D-500 stylus profler.

# **3 Results and discussion**

# **3.1 Morphology and chemical analysis**

The morphology of the Co/Cu co-doped flms are shown in Fig. [1](#page-2-0)a–d. It is evident from the images that, the surface morphology of the ZnO flms is signifcantly assumed by deposition method and annealing time. The obtained flms are composed of small spherical grains



<span id="page-2-0"></span>**Fig. 1** SEM images of (Co–Cu) co-doped ZnO thin films **a**  $x=0\%$ , **b**  $x=2\%$ , **c**  $x=4\%$  and **d**  $x=6\%$  as a function of (Co–Cu) contents

that present interstitial spaces; more apparent for the pure ZnO flm. For co-doped flms, it is notable that the interstitial spaces decrease, which may be an efect of the dopant cations that help to improve the flms densifcation. On the other hand, the EDAX analysis was performed to determine the elements composition of the obtained flms, (Fig. [2](#page-3-0)a–d). As observed, all flms contain the Zn and O elements, while in the co-doped ZnO flms, the cobalt (Co) and copper (Cu) elements are also observed (Figs. [2b](#page-3-0)–d), confrming its insertion in the ZnO crystal structure.

# **3.2 Structural characterization**

Figure [3](#page-4-0) displays the X-ray difraction patterns of the prepared flms. Note that, all flms have a well crystalline wurtzite hexagonal structure, typical of zinc oxide; that has been confrmed by the crystallographic card (*JCPDS No. 36-1451*). In addition, no additional phase of: Co, Cu, CuO, Cu<sub>2</sub>O, Co<sub>2</sub>O<sub>4</sub> and Co<sub>3</sub>O<sub>4</sub> was observed in the XRD spectra (Goktas



<span id="page-3-0"></span>**Fig. 2** EDAX spectra and table of concentration of (Co–Cu) co-doped ZnO thin films  $\mathbf{a} \times 0\%$ ,  $\mathbf{b} \times 2\%$ ,  $\mathbf{c}$  $x=4\%$  and  $\mathbf{d} x=6\%$  as a function of (Co–Cu) contents

<span id="page-4-0"></span>

[2018\)](#page-12-4). It is important to emphasize that all flms present a preferential orientation in the (002) direction. Many researchers believe that the more stable crystals level, as well as, the minimum free energy of surface, for ZnO flms, is associated to the (002) plane (Mhamdi et al. [2013;](#page-13-11) Baghdad et al. [2017](#page-12-10)).

The crystal lattice parameter, (*c*) (Lupan et al. [2010\)](#page-13-12), crystallite size (*D*) (Sengupta et al. [2013\)](#page-14-4), dislocation density ( $\delta$ ) (Williamson and Smallman [1956\)](#page-14-5), strain ( $\varepsilon_c$ ) and stress ( $\sigma_c$ ) (Mia et al. [2017](#page-13-13); Muchuweni et al. [2017\)](#page-13-14) were obtained using the subsequent formulas:

$$
d_{hkl} = \frac{\lambda}{2\sin}, \frac{1}{d_{hkl}^2} = \frac{4}{3} \left( \frac{h^2 + hk + k^2}{a^2} \right) + \frac{l^2}{c^2}
$$
 (1)

$$
u = \frac{a^2}{3c^2} + \frac{1}{4}, L = \sqrt{\left(\frac{a^2}{3} + \left(\frac{1}{2} - u\right)^2 c^2\right)}
$$
(2)

$$
D = \frac{0.9\lambda}{(\beta^2_{obs} - \beta^2_{ins})^{1/2} \cos\theta}, \delta = \frac{1}{D^2}
$$
 (3)

Here  $\lambda$  is the X-ray wavelength ( $\lambda_{CuK_a}$ =1.54060 Å),  $\beta = (\beta_{obs}^2 - \beta_{ins}^2)^{1/2}$  is the full width of the peak at half maximum ( $FWHM$ ) once corrected in radians and  $\theta$  is the Bragg diffraction angle.

$$
\varepsilon_c = \frac{C\text{film} - C\text{bulk}}{C\text{bulk}} 100\%, \sigma_c = -2.33 \times 10^{11} \left( \frac{C_{\text{film}} - C_{\text{bulk}}}{C_{\text{bulk}}} \right) \tag{4}
$$

wherec $c_{\text{film}}$  and  $c_{\text{bulk}}$  are the lattice parameters of the prepared films and bulk ZnO, respectively.

As shown in Table [1,](#page-5-0) the lattice parameter  $(c)$  values for co-doped films are inferior to the obtained for pure ZnO flms. The results were infuenced by the diference between the ionic radius of copper  $(r_{\text{Cu+2}}=0.72\text{\AA})$  and that of cobalt  $(r_{\text{Co+2}}=0.65\text{\AA})$ , compared to the zinc  $(r_{Zn+2}=0.74\text{\AA})$  (Sreedhar et al. [2016](#page-14-6); Benzitouni et al. [2017\)](#page-12-11). In addition, we note that the Co and Cu inclusion in the ZnO structure increased the

Samples	$2\theta$ (deg.)	<b>FWHM</b>	c(A)	D(nm)	$\delta (10^{-3}/\text{nm}^2)$	$\varepsilon_c (10^{-3})$	$\sigma$ <sub>o</sub> (GPa)
Un-doped $ZnO$	34.414	0.330	5.205	25.140	1.582	0.1096	$-0.2554$
ZnO:Co $2\%$ :Cu $2\%$	34.431	0.302	5.203	28.701	1.213	1.258	$-0.147$
$ZnO:Co 4\%:Cu 4\%$	34.436	0.301	5.202	28.131	1.263	1.254	$-0.114$
ZnO:Co $6\%$ :Cu $6\%$	34.425	0.252	5.204	34.472	0.841	1.050	$-0.186$

<span id="page-5-0"></span>**Table 1** The peak position 2 $\theta$ , FWHM, lattice parameter (a and c), grain size (D), dislocation density  $(\delta)$ , strain  $(\varepsilon_c)$  and stress  $(\sigma_c)$  of the (Co–Cu) co-doped ZnO thin films

crystalline size, ranging from 26.276 nm for the pure ZnO film to  $34.472$  nm for the  $6\%$ Co–Cu co-doped ZnO flm. This result could be attributed to the fact that, the co-doping may have ameliorated the crystal goodness, favoring the growth and nucleation mechanisms (Narayanan and Deepak [2018](#page-13-15); Kaphle and Hari [2018](#page-13-16)). In addition, the crystallite size increase may be related to the fact that the flms have preferential orientation in the c-axis. On the other hand, we note variations in the strain values, increasing the Co–Cu dopants concentration ratios. Finally, negative stress values point that the crystal structure is in a stress state due to the dopant atoms infuence, obtaining method and temperature, as well as the variance in thermal coefficient factor between the film and substrate (Joshi et al. [2016](#page-13-17)).

#### **3.3 Optical characterization**

Figure [4](#page-5-1) exhibits the optical transmittance and refectance spectra of the pure and codoped ZnO flms**.**In the visible spectrum, the optical transmittance of co-doped flms is relatively low, compared to the pure ZnO flm; around of 42% for the flm co-doped at 2% and 85% for pure ZnO flm. For wavelengths less than of 400 nm, the transmittance decreases rapidly, which confrms that flms have shift absorption. The optical absorption coefficient  $\alpha(\lambda)$  was determined for various photon energies using the transmission spectra and the equation (Gumus et al. [2006\)](#page-12-12):



<span id="page-5-1"></span>**Fig. 4 a** Optical transmittance and **b** refectance of (Co–Cu) co-doped ZnO thin flms as a function of wavelength

$$
\alpha = \frac{\text{Ln}(\frac{1}{T})}{t} \tag{5}
$$

Here T is the transmittance and t, is the thickness of the flms, that is equal to 150 nm in our case. The ZnO is a direct gap semiconductor. Thus, its energy-gap $(E_{\rho})$  could be deduced from the x interception of the linear extrapolation of the curve  $(ahv)^2$  as a function of photon energy radiation  $(h\nu)$  (inset of Fig. [5](#page-6-0)) by the Tauc's relationship (Kaphle and Hari [2018](#page-13-16)):

$$
(\alpha h v)^n = B(hv - Eg) \tag{6}
$$

where B is a constant and  $n=2$ , is used for the direct-gap energy.

In Fig. [5,](#page-6-0) the energy band-gap values  $(E_{\alpha})$  are presented as a function of Co–Cu dopants concentration. We can observe that the energy band gap decreases linearly increasing the Co–Cu concentration (3.37–3.16 eV for Co–Cu concentration ranging from 0.00 to 0.06). The energy-gap decrease can be explained by the atomic disorder (oxygen vacancy and zinc interstitial defects) generated in the ZnO structure due to the dopant cations inclusion. The defects provoke free electrons, with minor energy than the ZnO in the valence band, generating others electronic levels in the ZnO band gap, which will contribute to the energy band gap band reduction. In addition, some authors, attribute the variation in the energy gap to the charge transfer between the 4f level electrons and the conduction band or valence band of ZnO (Diouri et al. [1985](#page-12-13); Elilarassi and Chandrasekaran [2010;](#page-12-14) Li et al. [2011\)](#page-13-18). On the other hand, the small variance in the electronegativity between Cu (1.9), Co (1.88) and Zn (1.65) cations can also lead to a narrowing of the energy band gap (Ferhat et al. [2009\)](#page-12-15).



<span id="page-6-0"></span>**Fig. 5 a**: Plot of  $(\alpha h\nu)^2$  versus (hv) **b**: band-gap energy versus (Co–Cu) concentration

#### **3.3.1 Linear optical parameters**

The extinction coefficient (*k*), refractive index (*n*), real and imaginary parts ( $\varepsilon_r$  and  $\varepsilon_i$ ) of the dielectric constant and optical conductivity ( $\sigma_{\text{opt}}$ ) (Islma and Podder [2009](#page-13-19); Caglar et al. [2007,](#page-12-16) [2008\)](#page-12-17) have been calculated as follows:

$$
k = \frac{\alpha \lambda}{4\pi} \tag{7}
$$

$$
n = \left(\frac{1+R}{1-R}\right) + \sqrt{\frac{4R}{(1-R)^2} - k^2}
$$
 (8)

$$
\varepsilon_{\rm r} = n^2 - k^2 \varepsilon_{\rm i} = 2nk \tag{9}
$$

$$
\sigma_{\text{opt}} = \frac{\omega}{4\pi} \sqrt{\varepsilon_i^2 + (1 - \varepsilon_r)^2}
$$
 (10)

where  $\omega = \frac{hv}{\hbar\lambda}$ ,  $\alpha$  is the absorption coefficient and R represents the optical reflectance. The optical constants versus the wavelength are shown in Fig. [6](#page-8-0). It is to be noted that in the visible feld n is 1.75 for ZnO. This value increases for co-doped samples until it reaches about 2.5. Similar results have been reported in the literature by other authors (Hamidi et al. [2018](#page-12-18); Istrate et al. [2019\)](#page-13-20). Because of weak absorption, K is almost non-existent. The values of  $\varepsilon_r$  vary between 3 and 6 and the values of  $\varepsilon_i$  are almost zero. It can be said that the electric charge polarization varies with the electric range variation of incident wave. We also note an enhancement in the refractive index, damping factor, and the imaginary part appearance. This is owing to the attendance of great absorption and electron transfer in ultraviolet felds (Mahdhi et al. [2018\)](#page-13-21).

On the other hand, the Fig. [7](#page-9-0)a displays the change of optical conductivity for the Co–Cu co-doped ZnO flms in terms of the wavelength. As observed, the conductivity changes are like those of the absorption and the imaginary part of the dielectric constant. In addition, the optical conductivity was deduced in terms of the Co–Cu dopant percentages and are shown in Fig. [7](#page-9-0)b. Note that the optical conductivity values vary between  $1.68 \times 10^{16}$  and  $1.30 \times 10^{16}$  (1/s). Compared to the previous report, for Cu-doped ZnO thin films, there was an improvement due to the simultaneous Co and Cu dopant cations insertion in the ZnO crystal structure (Mohammedi et al. [2021](#page-13-6)).

The refractive index at elevated frequencies  $(n_{\infty}^2)$  (Walton and Moss [1963\)](#page-14-7), the individual oscillator energy of electronic transitions  $(E_0)$  and the dispersal energy  $(E_d)$  (Caglar et al. [2007\)](#page-12-16) were calculated using the following equations:

$$
\frac{n_{\infty}^2 - 1}{n^2 - 1} = 1 - \left(\frac{\lambda_0}{\lambda}\right)^2\tag{11}
$$

<span id="page-7-0"></span>
$$
n^2 = 1 + \frac{E_d E_0}{E_0^2 + (h\nu)^2}
$$
 (12)

Plotting  $(n_{\infty}^2-1)^{-1}$  in terms of  $\lambda^{-2}$ , the value of the  $n_{\infty}^2$  may be deduced from the inter-section with the ordinal axis of Fig. [8a](#page-9-1). Plotting  $(n^2 - 1)^{-1}$  in terms of  $(hv)^2$ , the values of



<span id="page-8-0"></span>**Fig. 6 a**: Refractive index n, **b**: extinction coefficient k, **c**: real part of dielectric constant  $\varepsilon$ <sub>r</sub> and **d**: imaginary part of dielectric constant  $\varepsilon$ <sub>i</sub>of the (Co–Cu) co-doped ZnO thin films with various wavelengths

 $E_0$  and  $E_d$  can be calculated by intersecting the order axis and the slope as shown in Fig. [8](#page-9-1). The  $E_0$ ,  $E_d$  and  $n_{\infty}$  values for the Co–Cu co-doped ZnO thin films are illustrated in the Table [2.](#page-9-2) Note that the values of  $E_d$  and  $n_{\infty}$  are improved increasing the Co–Cu concentration and these results are almost consistent for reported by Gao Xiao-Yong et al. (Gao et al. [2010\)](#page-12-19). All the values of  $E_0$  of the doped films are higher than that of the undoped film; on the other hand,  $E_0$  decreases with the increase of the doping concentration.



<span id="page-9-0"></span>**Fig. 7** Optical conductivity of (Co–Cu)co-doped ZnO, **a**: versus wavelength and **b**: versus Co–Cu concentration



<span id="page-9-1"></span>**Fig. 8 a**: The plot of  $(n^2 - 1)^{-1}$  various  $(\lambda)^{-2}$  and **b**: the plot of  $(n^2 - 1)^{-1}$  various  $(hv)^2$  of the (Co–Cu) codoped ZnO thin flms

<span id="page-9-2"></span>

#### **3.3.2 Nonlinear optical parameters**

The investigation of the interaction of the electromagnetic feld with the physical medium, where the interaction of the electric feld with the incidental wave is of non-linear polarization is shown by the subsequent formula (Frumar et al. [2003\)](#page-12-20)

$$
P_{NL} = \chi^{(1)}E + \chi^{(2)}E^2 + \dots \chi^{(n)}E^n \tag{13}
$$

Here,  $\chi^{(1)}$ ,  $\chi^{(2)}$  E<sup>2</sup> and  $\chi^{(3)}$  E<sup>3</sup> are the polarizabilities,  $\chi^{(1)}$  is the linear optical susceptibility, and  $\chi^{(2)}$  and  $\chi^{(3)}$  are the second- and third-order nonlinear optical susceptibility, respectively.

The n becomes non-linear according to the following equation,

$$
n(\lambda) = n_0(\lambda) + n^{(2)}(E^2)
$$
\n(14)

Here ,  $n^{(0)}$  is linear, n and  $n^{(2)}$  is nonlinear. The n is allied to the electric field power. Various quasi-empirical equations are nominated to calculate the third-order non-linear optical susceptibility  $\chi^{(3)}$  and the non-linearn<sup>(2)</sup>. Amongst these relations, one may obtain the Miller formula generalized in the subsequent relation (Ticha and Tichy [2002](#page-14-8)),

$$
\chi^{(3)} = A(\chi^{(1)})\tag{15}
$$

According to Adair et al. (Ferhat et al. [2009](#page-12-15)), the valueof the constant (*A*) is equal to  $1.79 \times 10^{-10}$  (for  $\chi^{(1)}$  in esu). For a different type of materials,

$$
\chi^{(1)} = \frac{(n^2 - 1)}{4\pi} \tag{16}
$$

Considering the Eq. ([13](#page-7-0)), at small frequencies hv $\rightarrow$ 0 and n=n<sub>0</sub>, ( $\chi^{(1)}$ ) is explained by:

$$
\chi^{(1)} = \frac{E_d}{E_0 4\pi} \tag{17}
$$

$$
n^{(2)} = \frac{12\pi \chi^{(3)}}{n_0} \tag{18}
$$

We have calculated the quantities of  $\chi^{(1)}$ ,  $\chi^{(3)}$  and  $n^{(2)}$  in terms of the wavelength (Fig. [9a](#page-10-0)–c). We notice that the values of these parameters increase in the ultraviolet feld, but they are almost constant in the visible feld. The NLO constants values increase with the Co–Cu co-dopant cations insertion (Table [3](#page-11-2)). This phenomenon is related to a crystallization improved of the samples (Table [1](#page-5-0)). Everything indicates that our ZnO thin flms co-doped with Co and Cu are candidate for NLO applications.

<span id="page-10-0"></span>

$n^{(2)}$ , esu
$4.161 \times 10^{-10}$
$4.808 \times 10^{-10}$
$9.326 \times 10^{-10}$
$1.109 \times 10^{-9}$
$1.89 - 9.119 \times 10^{-10}$
$0.5 \times 10^{-10} - 1 \times 10^{-9}$
$0.25 - 4.59 \times 10^{-12}$

<span id="page-11-2"></span>**Table 3** Nonlinear optical parameters of reported and present work on ZnO thin flms

# **4 Conclusions**

In the present study, thin films of ZnO co-doped with cations of  $Co^{2+}$  and  $Cu^{2+}$  were obtained utilizing the sol–gel method and spin coating technique. The morphological, structural, and optical linear and nonlinear properties are analyzed in detail. The SEM images revealed that the pure ZnO flm is composed by small spherical grains that present interstitial spaces, while the flms obtained from the simultaneous Co and Cu insertion in the ZnO structure are more dense and interstitial spaces disappear. The EDAX data confrm the attendance of Co, Cu, Zn and O elements in the ZnO thin flms. The X-ray difraction patterns confrmed the single-phase formation of ZnO and preferential orientation in the (002) direction. In addition, the  $Zn^{2+}$  cations by  $Co^{2+}$  and  $Cu^{2+}$  cations replacement, provokes signifcant variations in the lattice parameter (c), crystallite size (D), dislocation density (δ), strain (ε<sub>c</sub>) and stress ( $\sigma_c$ ) of the hexagonal structure wurtzite from ZnO. In general, the results obtained in this work provide new alternatives for designing thin flms with optoelectronics applications. This is because the layers have the desired nonlinear optical properties to efectively transparent conductive screens.

**Author contributions** AM: Performed the experiences of this work. OM: Performed the experiences of this work. MI: Supervised and developed the experience. BM and RP-G: Verifed the development of experiences. NB: Supervised the fndings of this work. All authors discussed the results and contributed to the fnal manuscript.

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### **Declarations**

**Confict of interest** The authors declare that they have no conficts of interest.

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